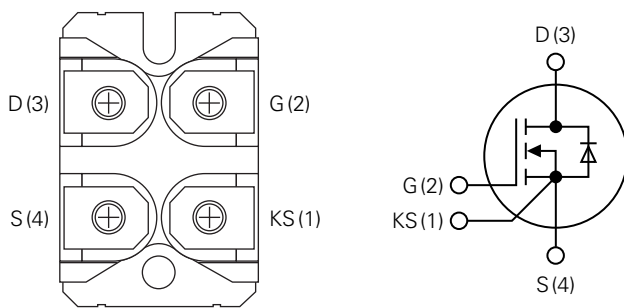


**IXFN55N120SK**

1200 V, 32 mΩ, 54 A SiC Power MOSFET

E72873

**Pinout Diagram** (SOT-227B miniBLOC)**D:** Drain; **G:** Gate; **S:** Source; **KS:** Kelvin Source; **Backside:** Isolated**Features & Benefits:**

- Latest Generation SiC MOSFET with Low  $R_{DS(on)}$
- Ideal for High Frequency Switching Applications
- Compatible with 15 V Gate Drive Voltage
- Real Kelvin Source Connection

**Applications:**

- Solar Inverters
- DC/DC Converters
- Motor Drives
- Switch Mode Power Supplies
- UPS
- Battery Chargers
- Induction Heating

**Package:**

- Isolation Voltage: 2500 V AC
- RoHS Compliant
- Epoxy Meets UL 94V-0
- Baseplate with Aluminum Nitride Isolation

**Product Summary**

Characteristic	Value	Unit
$I_{D25}$	54	A
$V_{DSS}$	1200	V
$R_{DS(on)typ}$	32	mΩ

## MOSFET

Symbol	Characteristic	Conditions	Value			Unit	
			Min.	Typ.	Max.		
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 19\text{ }\mu\text{A}, T_{VJ} = 25\text{ }^\circ\text{C}$	1200	–	–	V	
$V_{GS}$	Gate-Source Voltage	Continuous	$T_{VJ} = 25\text{ }^\circ\text{C}$	–4	–	15	V
		Transient		–8	–	19	V
$I_{D25}$	Continuous Drain Current	$V_{GS} = 15\text{ V}$	$T_C = 25\text{ }^\circ\text{C}$	–	–	54	A
$I_{D80}$			$T_C = 80\text{ }^\circ\text{C}$	–	–	43	
$I_{D100}$			$T_C = 100\text{ }^\circ\text{C}$	–	–	38	
$R_{DS(on)}$	Static Drain-Source on Resistance	$I_D = 40\text{ A}, V_{GS} = 15\text{ V}$	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	32	42	m $\Omega$
			$T_{VJ} = 150\text{ }^\circ\text{C}$	–	53	–	
$V_{GS(th)}$	Gate Threshold Voltage	$I_D = 12\text{ mA}, V_{GS} = V_{DS}$	$T_{VJ} = 25\text{ }^\circ\text{C}$	1.8	2.5	3.6	V
			$T_{VJ} = 150\text{ }^\circ\text{C}$	–	2.1	–	
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	1	20	$\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage Current	$V_{DS} = 0\text{ V}, V_{GS} = 15\text{ V}$	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	–	250	nA
$R_{G(int)}$	Internal Gate Resistance	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}, \text{ESR of } C_{iss}$	–	1.7	–	$\Omega$	
$T_{VJ,op}$	Virtual Junction Temperature	–	–40	–	150	$^\circ\text{C}$	
$T_{VJ,max}$	Maximum Virtual Junction Temperature	–	–	–	175	$^\circ\text{C}$	
$C_{iss}$	Input Capacitance	$V_{DS} = 1000\text{ V}, V_{GS} = 0\text{ V},$ $f = 100\text{ kHz}$	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	3360	–	pF
$C_{oss}$	Output Capacitance			–	130	–	pF
$C_{rss}$	Reverse Transfer Capacitance			–	8	–	pF
$Q_g$	Total Gate Charge	$V_{DS} = 800\text{ V}, I_D = 40\text{ A},$ $V_{GS} = -4 / 15\text{ V}$	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	107	–	nC
$Q_{gs}$	Gate-Source Charge			–	37	–	nC
$Q_{gd}$	Gate-Drain Charge			–	33	–	nC
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching</b> $V_{DS} = 800\text{ V}, V_{GS} = -4 / 15\text{ V},$ $I_D = 40\text{ A}, R_{G,ext} = 5\text{ }\Omega,$ Free Wheeling Diode: Body Diode	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	24	–	ns
			$T_{VJ} = 150\text{ }^\circ\text{C}$	–	22	–	
$t_r$	Current Rise Time		$T_{VJ} = 25\text{ }^\circ\text{C}$	–	23	–	ns
			$T_{VJ} = 150\text{ }^\circ\text{C}$	–	27	–	
$t_{d(off)}$	Turn-off Delay Time		$T_{VJ} = 25\text{ }^\circ\text{C}$	–	41	–	ns
			$T_{VJ} = 150\text{ }^\circ\text{C}$	–	46	–	
$t_f$	Current Fall Time		$T_{VJ} = 25\text{ }^\circ\text{C}$	–	11	–	ns
			$T_{VJ} = 150\text{ }^\circ\text{C}$	–	16	–	
$E_{on}$	Turn-on Energy per Pulse		$T_{VJ} = 25\text{ }^\circ\text{C}$	–	562	–	$\mu\text{J}$
			$T_{VJ} = 150\text{ }^\circ\text{C}$	–	813	–	
$E_{off}$	Turn-off Energy per Pulse	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	162	–	$\mu\text{J}$	
		$T_{VJ} = 150\text{ }^\circ\text{C}$	–	166	–		
$E_{rec}$	Reverse Recovery Losses at Turn-off	$T_{VJ} = 25\text{ }^\circ\text{C}$	–	110	–	$\mu\text{J}$	
		$T_{VJ} = 150\text{ }^\circ\text{C}$	–	372	–		

## Thermal Characteristics

Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
$R_{th,JC}$	Thermal Resistance, Junction-to-Case	$T_{VJ} = 125\text{ }^\circ\text{C}$	–	–	0.71	K/W
$R_{th,JH}$	Thermal Resistance, Junction-to-Heatsink	With heatsink compound $\lambda = 0.67\text{ W/mK}$	–	0.79	–	K/W

## Source-Drain Diode

Symbol	Characteristic	Conditions	Value			Unit	
			Min.	Typ.	Max.		
$V_{SD}$	Forward Voltage Drop	$I_F = 20 \text{ A}; V_{GS} = -4 \text{ V}$	$T_{VJ} = 25 \text{ }^\circ\text{C}$	-	4.6	-	V
			$T_{VJ} = 150 \text{ }^\circ\text{C}$	-	4.2	-	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = -4 \text{ V}; I_F = 40 \text{ A}; V_R = 800 \text{ V}$ MOSFET Gate Drive: $V_{GS} = -4 / +15 \text{ V}; R_G = 5 \text{ } \Omega$	$T_{VJ} = 25 \text{ }^\circ\text{C}$	-	15	-	ns
			$T_{VJ} = 150 \text{ }^\circ\text{C}$	-	20	-	
$Q_{rm}$	Reverse Recovery Charge (Intrinsic Diode)	$V_{GS} = -4 \text{ V}; I_F = 40 \text{ A}; V_R = 800 \text{ V}$ MOSFET Gate Drive: $V_{GS} = -4 / +15 \text{ V}; R_G = 5 \text{ } \Omega$	$T_{VJ} = 25 \text{ }^\circ\text{C}$	-	337	-	$\mu\text{C}$
			$T_{VJ} = 150 \text{ }^\circ\text{C}$	-	721	-	
$I_{rm}$	Max. Reverse Recovery Current	$V_{GS} = -4 / +15 \text{ V}; R_G = 5 \text{ } \Omega$	$T_{VJ} = 25 \text{ }^\circ\text{C}$	-	39	-	A
			$T_{VJ} = 150 \text{ }^\circ\text{C}$	-	65	-	
$dl_f/dt$	Current Slew Rate	$V_{GS} = -4 / +15 \text{ V}; R_G = 5 \text{ } \Omega$	$T_{VJ} = 25 \text{ }^\circ\text{C}$	-	5257	-	A/ $\mu\text{s}$
			$T_{VJ} = 150 \text{ }^\circ\text{C}$	-	5758	-	

**Note:** When using SiC Body Diode the maximum recommended  $V_{GS} = -4\text{V}$

## Package SOT-227B (miniBLOC)

Symbol	Characteristic	Conditions	Value			Unit	
			Min.	Typ.	Max.		
$I_{RMS}$	RMS Current	Per Terminal	-	-	100	A	
$T_{stg}$	Storage Temperature	-	-40	-	150	$^\circ\text{C}$	
$T_{op}$	Operation Temperature	-	-40	-	150	$^\circ\text{C}$	
$M_D$	Mounting Torque <sup>1</sup>	Screws to Heatsink	-	-	1.5	Nm	
		Terminal Connection Screws	-	-	1.3	Nm	
$V_{ISOL}$	Isolation Voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}, 1 \text{ sec.}$	3000	-	-	V	
		$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}, 1 \text{ minute}$	2500	-	-	V	
$d_{Spp/APP}$ $d_{Spb/APb}$	Clearance Distance Through Air	Terminal to Terminal	Between Pin 1 to 2	7.1	-	-	mm
			Between Pin 3 to 4				
			Between Pin 2 to 3	3.2	-	-	mm
			Between Pin 4 to 1				
	Creepage Distance on Surface	Terminal to Terminal (With Nut)	Between Pin 1 to 2	9.6	-	-	mm
			Between Pin 3 to 4				
			Between Pin 2 to 3	10.5	-	-	mm
			Between Pin 4 to 1				
Clearance Distance Through Air	Terminal to Backside Plane	For All Terminals	8.6	-	-	mm	
Creepage Distance on Surface	Terminal to Backside Tab		10.5	-	-		
W	Weight	-	-	30	-	g	

**1)** For further information see application note "[Handling and Mounting Littelfuse miniBLOC - SOT227B](#)"

**Characteristic Curves**

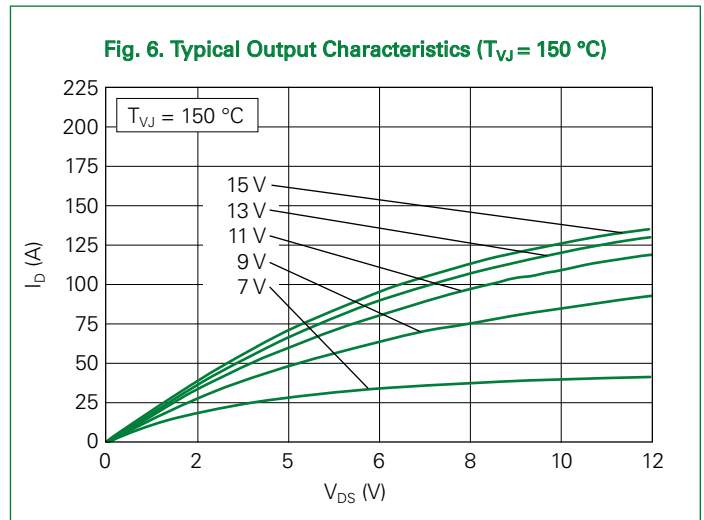
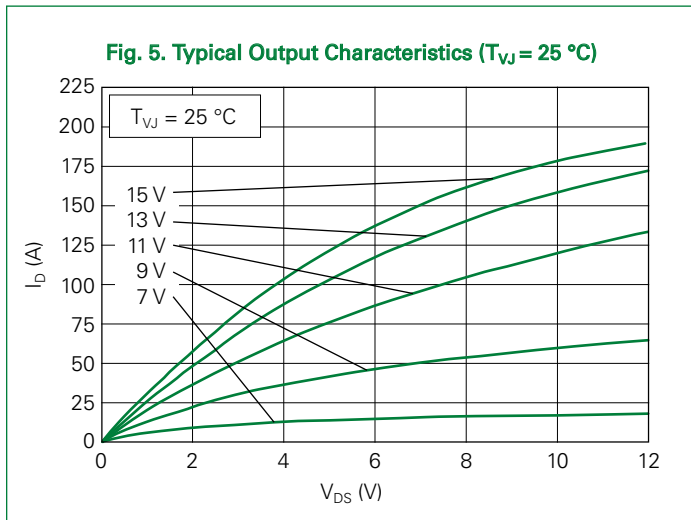
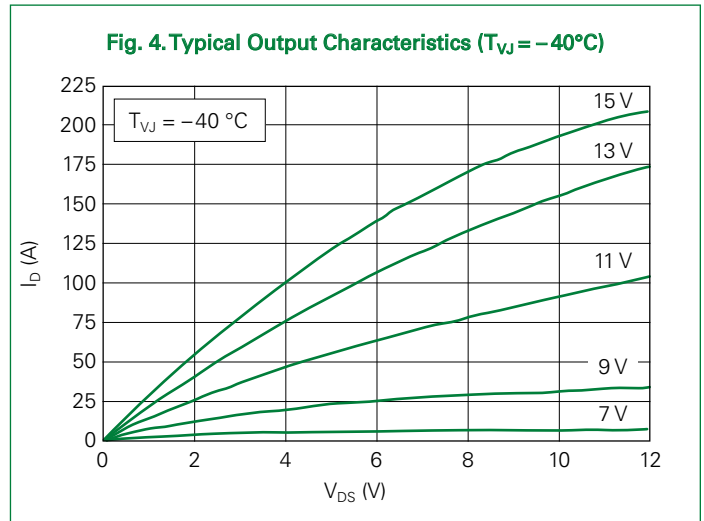
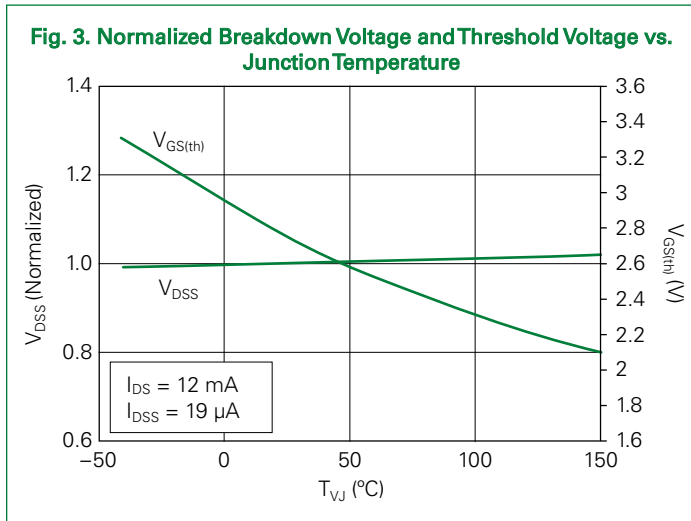
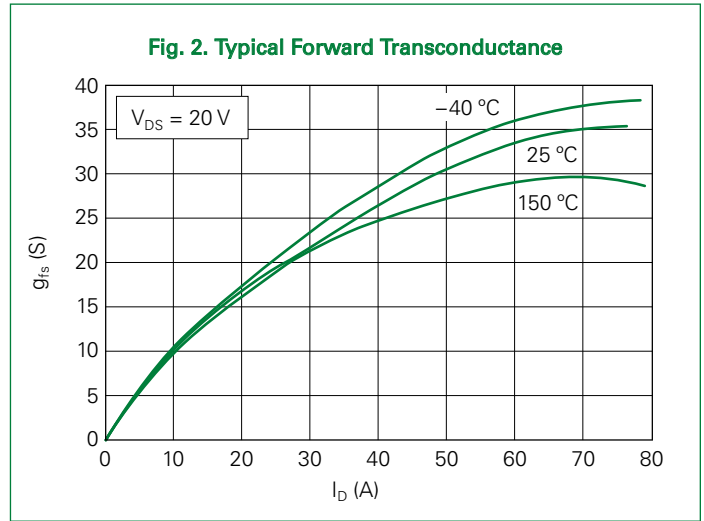
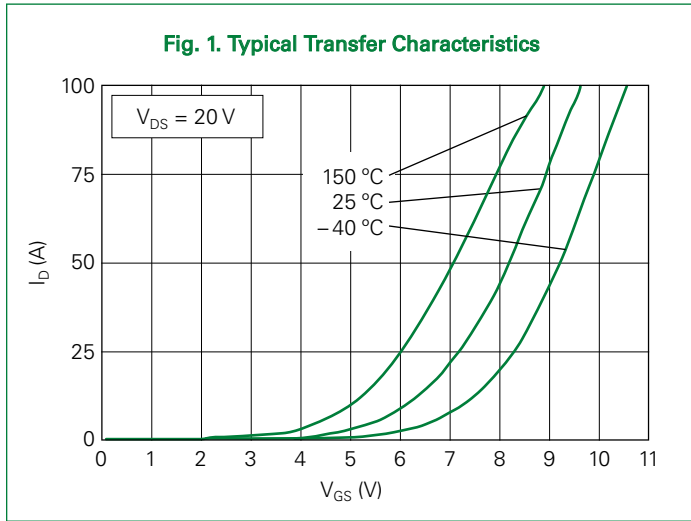


Fig. 7.  $R_{DS(on)}$  vs. Junction Temperature

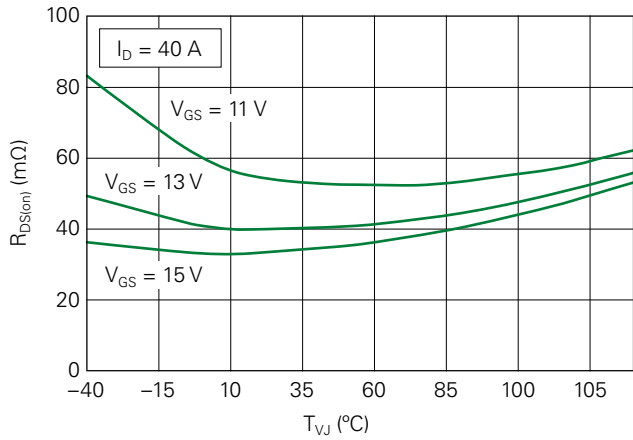


Fig. 8.  $R_{DS(on)}$  Normalised vs. Junction Temperature

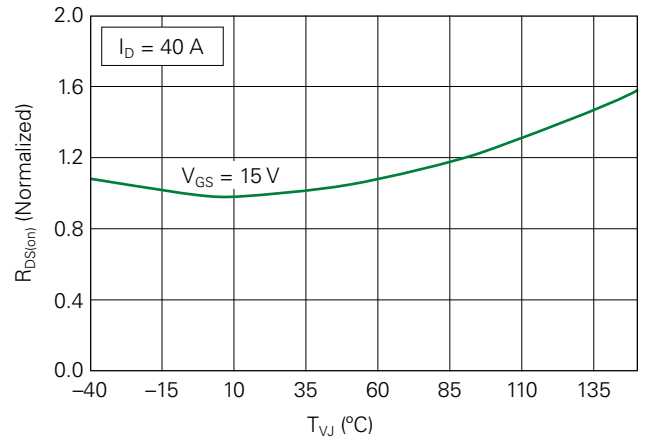


Fig. 9.  $R_{DS(on)}$  vs. Drain Current

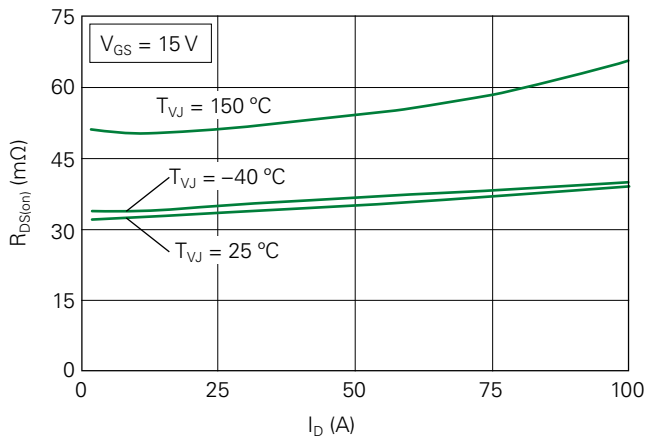


Fig. 10. Typical Reverse Conduction Characteristics ( $T_{VJ} = -40^\circ\text{C}$ )

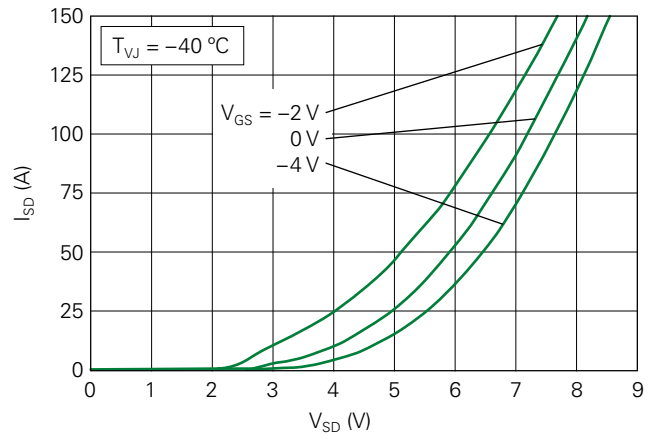


Fig. 11. Typical Reverse Conduction Characteristics ( $T_{VJ} = 25^\circ\text{C}$ )

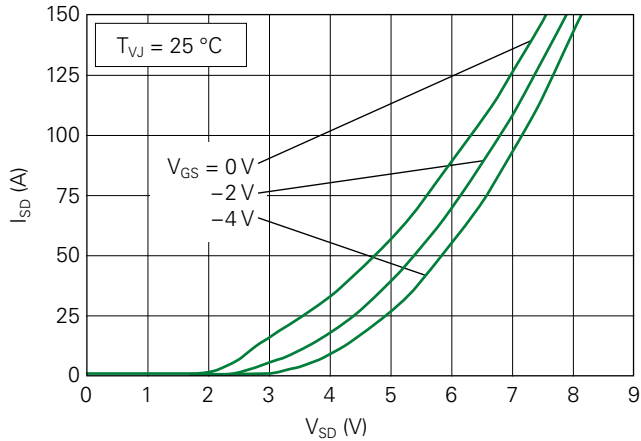


Fig. 12. Typical Reverse Conduction Characteristics ( $T_{VJ} = 150^\circ\text{C}$ )

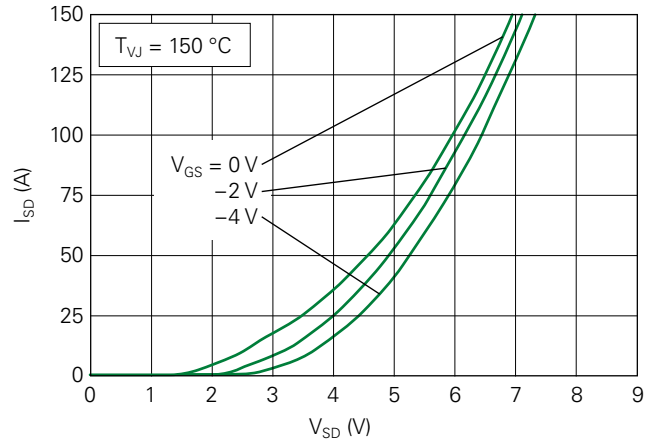


Fig. 13. Typical Junction Capacitances

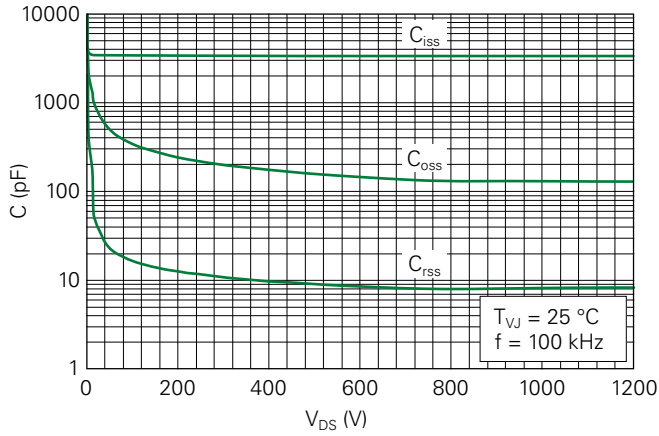


Fig. 14. Power Dissipation vs. Case Temperature

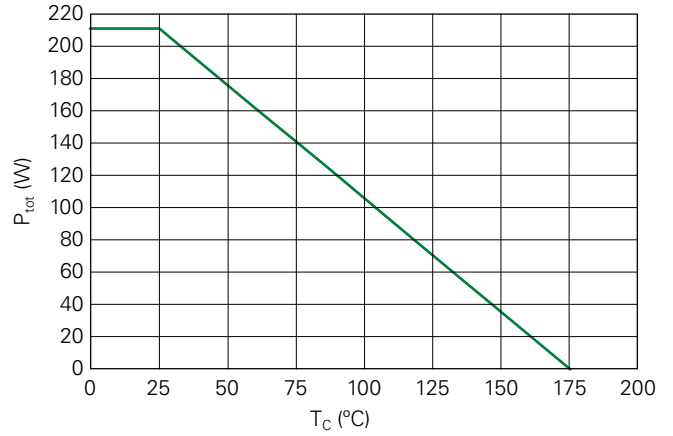


Fig. 15. Drain Current vs. Case Temperature

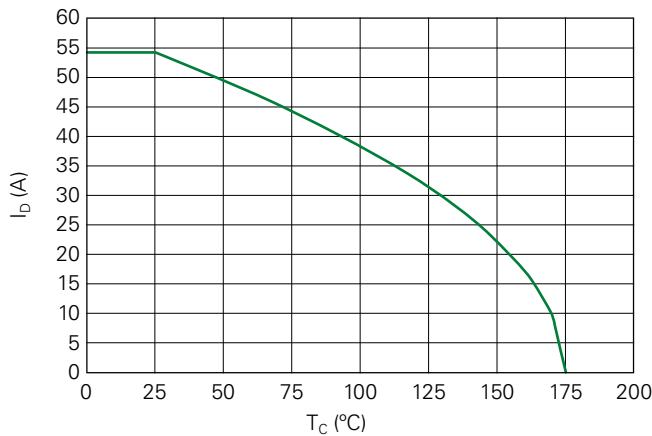


Fig. 16. Typical Switching Energy vs. Drain Current

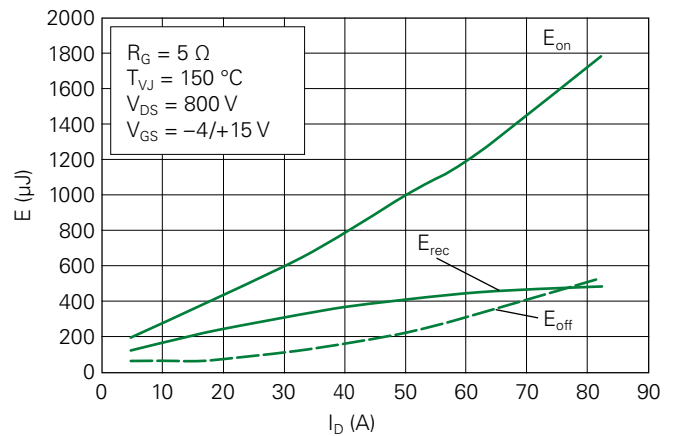


Fig. 17. Typical Switching Energy vs. Junction Temperature

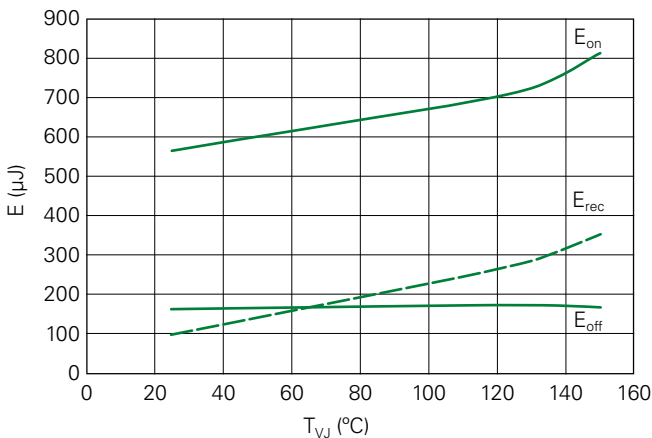
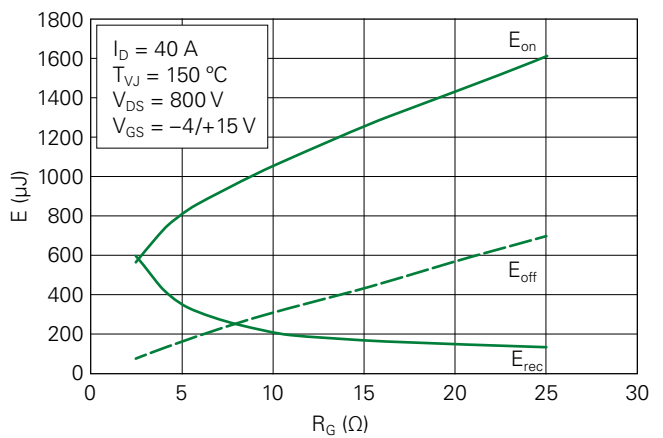
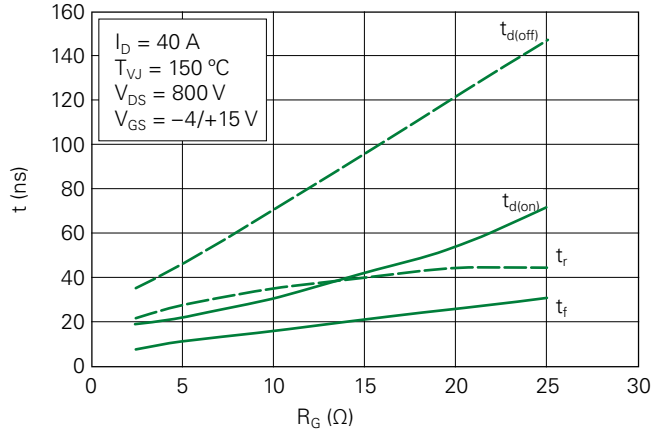


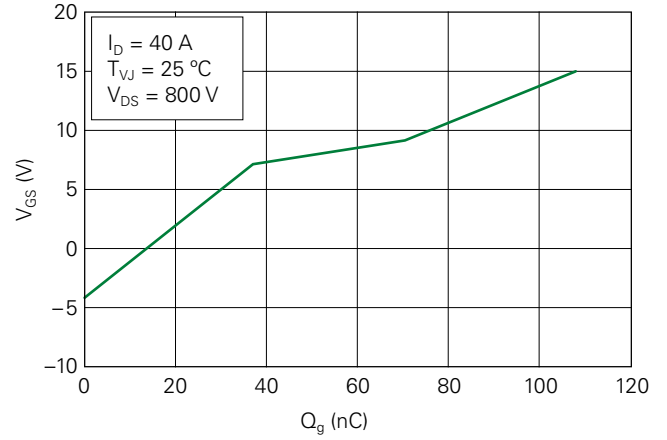
Fig. 18. Typical Switching Energy vs. External Gate Resistor



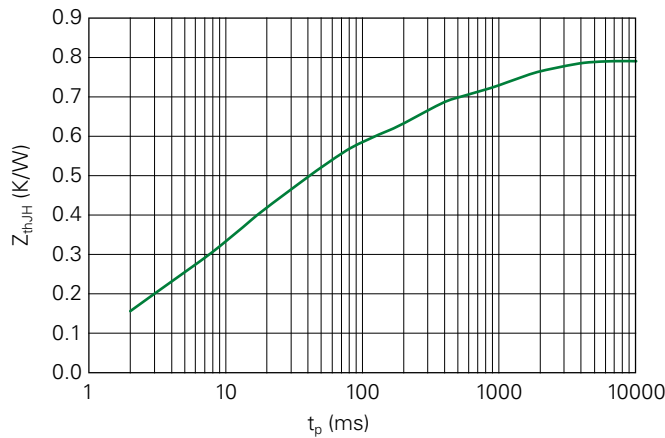
**Fig. 19. Typical Switching Time vs. External Gate Resistor**



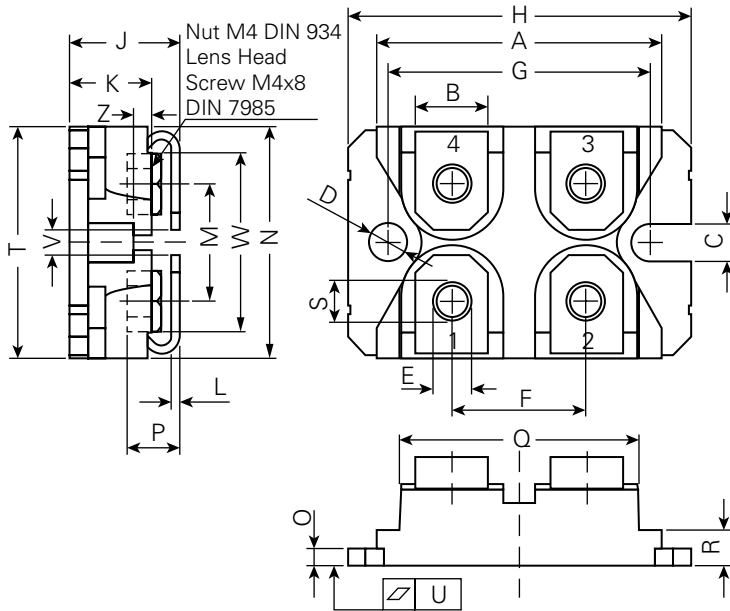
**Fig. 20. Typical Turn on Gate Charge Trendline**



**Fig. 21. Typical Transient Thermal Impedance**

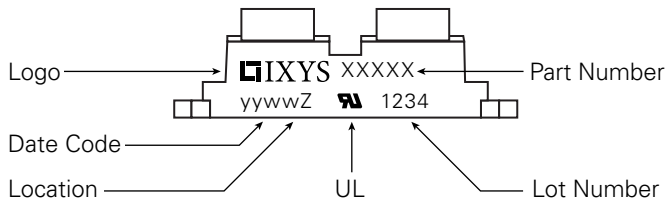


## Part Outline Drawing (SOT-227B miniBLOC)



Symbol	Inches		Millimeters	
	Min.	Max.	Min.	Max.
A	1.240	1.255	31.50	31.88
B	0.307	0.323	7.80	8.20
C	0.161	0.169	4.09	4.29
D	0.161	0.169	4.09	4.29
E	0.161	0.169	4.09	4.29
F	0.587	0.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.488	1.505	37.80	38.23
J	0.460	0.481	11.68	12.22
K	0.351	0.378	8.92	9.60
L	0.029	0.033	0.74	0.84
M	0.492	0.516	12.50	13.10
N	0.990	1.001	25.15	25.42
O	0.077	0.084	1.95	2.13
P	0.195	0.244	4.95	6.20
Q	1.045	1.059	26.54	26.90
R	0.155	0.167	3.94	4.42
S	0.179	0.191	4.55	4.85
T	0.968	0.994	24.59	25.25
U	-0.002	0.004	-0.05	0.10
V	0.126	0.217	3.20	5.50
W	0.780	0.830	19.81	21.08
Z	.098	0.106	2.50	2.70

## Part Number and Marking



## Ordering Information

Ordering	Part Number	Marking on Product	Delivering Mode	Base Quantity	Ordering Code
Standard	IXFN55N120SK	IXFN55N120SK	Tube	10	IXFN55N120SK

## Disclaimer Notice

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Part of:

